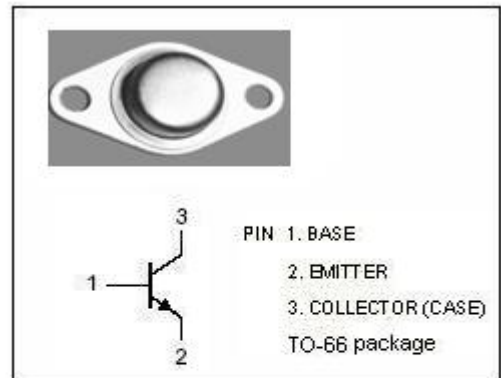


**isc Silicon NPN Power Transistor**
**BDY79**
**DESCRIPTION**

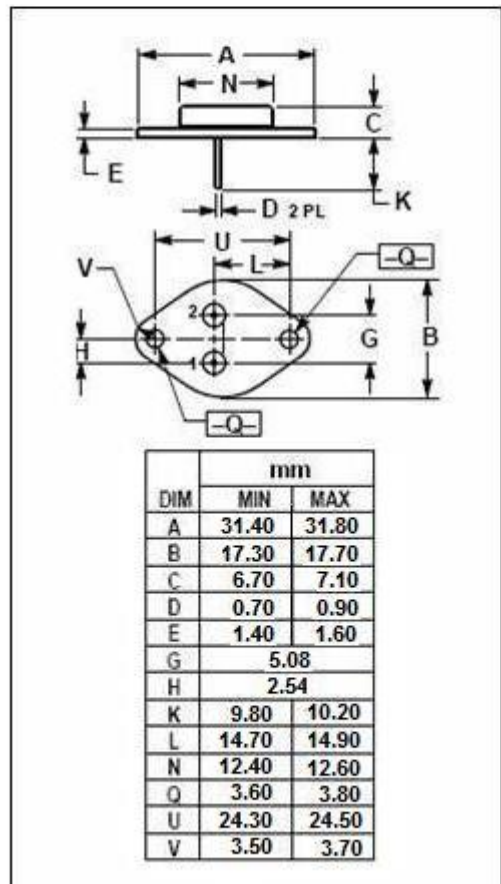
- Continuous Collector Current- $I_C= 4A$
- Collector Power Dissipation-  
:  $P_C= 25W @T_C= 25^\circ C$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for general purpose switching and amplifier applications.


**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	150	V
$V_{CEX}$	Collector-Emitter Voltage $V_{BE}= -1.5V$	150	V
$V_{CEO}$	Collector-Emitter Voltage	120	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	4	A
$I_B$	Base Current-Continuous	2	A
$P_C$	Collector Power Dissipation@ $T_C=25^\circ C$	25	W
$T_J$	Junction Temperature	200	$^\circ C$
$T_{stg}$	Storage Temperature	-65~200	$^\circ C$


**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	7.0	$^\circ C/W$

**isc Silicon NPN Power Transistor****BDY79****ELECTRICAL CHARACTERISTICS**T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	120		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	150		V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 0.5A; I <sub>B</sub> = 50mA		1.0	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 1A		3.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 4V		2.0	V
I <sub>CEX</sub>	Collector Cutoff Current	V <sub>CE</sub> = 150V; V <sub>BE</sub> = -1.5V V <sub>CE</sub> = 150V; V <sub>BE</sub> = -1.5V, T <sub>C</sub> =150°C		1.0 5.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0		1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 4V	25	100	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 4V	5		
f <sub>T</sub>	Current Gain-Bandwidth Product	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 10V	8		MHz

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